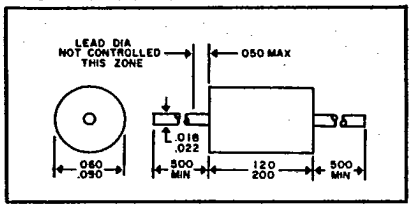
ZENER DIODES

DO-35 Case



250mW — DO-35 Case

Type†	Nominal Zener Voltage	Test Current	Maximum‡ Dynamic Impedance	Typical Temperature Coefficient
	V_Z @ I_{ZT}	I_{ZT}	Z_{ZT} @ I_{ZT}	T_C
	V	mA	Ω	%/°C
BZY83C6V8	6.8	5	8	.070
BZY83C7V5	7.5		6	.070
BZY83C8V2	8.2		7	.070
BZY83C9V1	9.1		10	.080
BZY83C10	10.0	5	15	.080
BZY83D10	10.0		15	.080
BZY83C11	11.0		20	.080
BZY83C12	12.0		30	.090
BZY83C13V5	13.5		30	.090
BZY83C15	15.0	5	55	.090
BZY83C16V5	16.5		75	.095
BZY83C18	18.0		110	.095
BZY83C20	20.0		150	.100
BZY83C22	22.0		170	.100
BZY83C24V5	24.5	5	200	.100

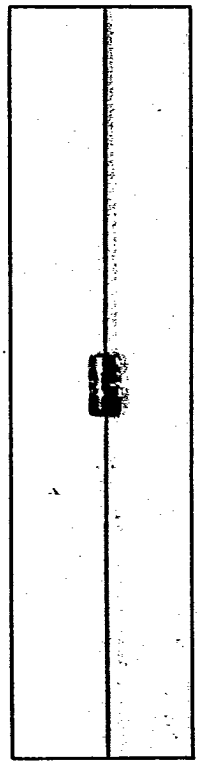
250mW — DO-35 Case

Type†	Nominal Zener Voltage	Test Current	Maximum‡ Dynamic Impedance	Typical Temperature Coefficient
	V_Z @ I_{ZT}	I_{ZT}	Z_{ZT} @ I_{ZT}	T_C
	V	mA	Ω	%/°C
BZY85C6V8	6.8	5	8	.070
BZY85C7V5	7.5		7	.070
BZY85D8V2	8.2		8	.070
BZY85C9V1	9.1		10	.080
BZY85C10	10	5	15	.080
BZY85C11	11		20	.080
BZY85C12	12		20	.090
BZY85C13V5	13		26	.090
BZY85C16V5	16		40	.095
BZY85C18	18	5	55	.095
BZY85C20	20		55	.100
BZY85C22	22		55	.100
BZY85C24V5	24		80	.100

†Standard tolerance of ±5%.

‡Zener impedance is derived from the 1kHz voltage created when AC current with RMS value of 10% of DC zener test current is superimposed on the test current.

DO-35 Case



400mW — DO-35 Case

Type†	Nominal Zener Voltage	Test Current	Maximum‡ Dynamic Impedance	Typical Temperature Coefficient
	V_Z @ I_{ZT}	I_{ZT}	Z_{ZT} @ I_{ZT}	T_C
	V	mA	Ω	%/°C
1N3506	3.3	20	24	−.07
1N3507	3.6		22	−.065
1N3508	3.9		20	−.060
1N3509	4.3		18	−.055
1N3510	4.7	20	16	−.030
1N3511	5.1		14	±.030
1N3512	5.6		8	.038
1N3513	6.2		3	.045
1N3514	6.8		3	.035
1N3515	7.5	10	4	.045
1N3516	8.2		5	.052
1N3517	9.1		6	.056
1N3518	10.0		7	.060
1N3519	11		8	.065
1N3520	12		10	.070
1N3521	13	5	12	.075
1N3522	15		14	.080
1N3523	16		16	.085
1N3524	18		18	.090
1N3525	20		20	.098
1N3526	22		35	.100
1N3527	24		38	.100
1N3528	27	4	40	.100
1N3529	30	4	48	.100
1N3530	33	3	50	.100

†Standard tolerance of ±5%.

‡Zener impedance is derived from the 1kHz voltage created when AC current with RMS value of 10% of DC zener test current is superimposed on the test current.

SEMICONDUCTORS